

FEATURES

- High-speed access time: 12, 15, 20, 25 ns
- Low active power: 600 mW (typical)
- Low standby power: 500 μ W (typical) CMOS standby
- Output Enable ($\overline{OE}$) and two Chip Enable ($\overline{CE1}$ and $\overline{CE2}$) inputs for ease in applications
- Fully static operation: no clock or refresh required
- TTL compatible inputs and outputs
- Single 5V ($\pm 10\%$) power supply
- Low power version available: IS61C1024L
- Commercial and industrial temperature ranges available

DESCRIPTION

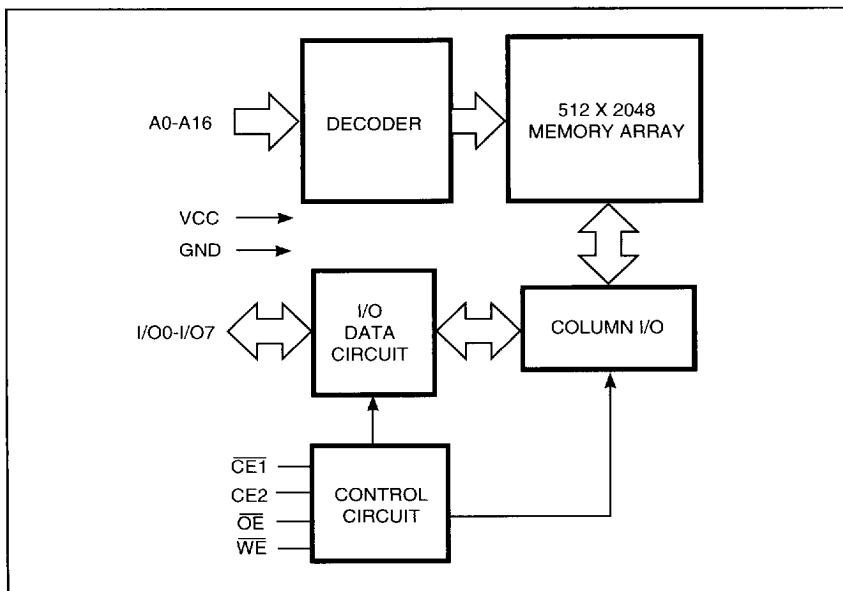
The ISSI IS61C1024 and IS61C1024L are very high-speed, low power, 131,072-word by 8-bit CMOS static RAMs. They are fabricated using ISSI's high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields higher performance and low power consumption devices.

When $\overline{CE1}$ is HIGH or $\overline{CE2}$ is LOW (deselected), the device assumes a standby mode at which the power dissipation can be reduced down to 500 μ W (typical) at CMOS input levels.

Easy memory expansion is provided by using two Chip Enable inputs, $\overline{CE1}$ and $\overline{CE2}$. The active LOW Write Enable ($\overline{WE}$) controls both writing and reading of the memory.

The IS61C1024 and IS61C1024L are available in 32-pin 300-mil and 400-mil plastic DIP and SOJ packages.

FUNCTIONAL BLOCK DIAGRAM



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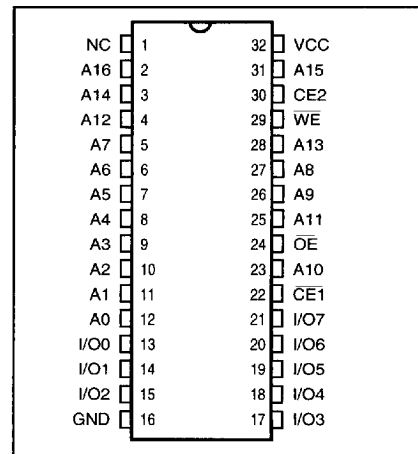
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2-65

PIN DESCRIPTIONS

A0-A16	Address Inputs
$\overline{CE1}$	Chip Enable 1 Input
CE2	Chip Enable 2 Input
$\overline{OE}$	Output Enable Input
$\overline{WE}$	Write Enable Input
I/O0-I/O7	Input/Output
Vcc	Power
GND	Ground

PIN CONFIGURATION
32-Pin DIP and SOJ

OPERATING RANGE

Range	Ambient Temperature	Vcc ⁽¹⁾
Commercial	0°C to +70°C	5V ± 10%
Industrial	-40°C to +85°C	5V ± 10%

Notes:

1. Vcc = 5V ± 5% for 12 ns devices.

TRUTH TABLE

Mode	$\overline{WE}$	$\overline{CE1}$	CE2	$\overline{OE}$	I/O Operation	Vcc Current
Not Selected	X	H	X	X	High-Z	Isb1, Isb2
(Power-down)	X	X	L	X	High-Z	Isb1, Isb2
Output Disabled	H	L	H	H	High-Z	Icc1, Icc2
Read	H	L	H	L	DOUT	Icc1, Icc2
Write	L	L	H	X	DIN	Icc1, Icc2

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
TBIAS	Temperature Under Bias	-55 to +125	°C
TSTG	Storage Temperature	-65 to +150	°C
PT	Power Dissipation	1.5	W
IOUT	DC Output Current (LOW)	20	mA

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE^(1,2)

Symbol	Parameter	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 0V	5	pF
COUT	Output Capacitance	VOUT = 0V	7	pF

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: TA = 25°C, f = 1 MHz, Vcc = 5.0V.

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -4.0 mA	2.4	—	V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA	—	0.4	V
V _{IH}	Input HIGH Voltage		2.2	V _{CC} + 0.5	V
V _{IL}	Input LOW Voltage ⁽¹⁾		-0.3	0.8	V
I _{LI}	Input Leakage	GND ≤ V _{IN} ≤ V _{CC}	Com. Ind.	-2 5	μA
I _{LO}	Output Leakage	GND ≤ V _{OUT} ≤ V _{CC} Outputs Disabled	Com. Ind.	-2 5	μA

Notes:

1. V_{IL} = -3.0V for pulse width less than 10 ns.

IS61C1024 POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range, Standard Version)

Symbol	Parameter	Test Conditions		-12 ns		-15 ns		-20 ns		-25 ns		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
I _{CC1}	V _{CC} Operating Supply Current	V _{CC} = Max., I _{OUT} = 0 mA, f = 0	Com. Ind.	— —	140 140	— —	140 140	— —	140 140	— —	140 140	mA
I _{CC2}	V _{CC} Dynamic Operating Supply Current	V _{CC} = Max., I _{OUT} = 0 mA, f = f _{MAX}	Com. Ind.	— —	220 220	— —	200 200	— —	170 170	— —	150 150	mA
I _{SB1}	TTL Standby Current (TTL Inputs)	V _{CC} = Max., V _{IN} = V _{IH} or V _{IL} CE1 ≥ V _{IH} or CE2 ≤ V _{IL} , f = 0	Com. Ind.	— —	40 60	— —	40 60	— —	40 60	— —	40 60	mA
I _{SB2}	CMOS Standby Current (CMOS Inputs)	V _{CC} = Max., CE1 ≥ V _{CC} - 0.2V, CE2 ≤ 0.2V, V _{IN} ≥ V _{CC} - 0.2V, or V _{IN} ≤ 0.2V, f = 0	Com. Ind.	— —	30 40	— —	30 40	— —	30 40	— —	30 40	mA

IS61C1024L POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range, Low Power Version)

Symbol	Parameter	Test Conditions		-12 ns		-15 ns		-20 ns		-25 ns		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
I _{CC1}	V _{CC} Operating Supply Current	V _{CC} = Max., I _{OUT} = 0 mA, f = 0	Com. Ind.	— —	85 110	— —	85 110	— —	85 110	— —	85 110	mA
I _{CC2}	V _{CC} Dynamic Operating Supply Current	V _{CC} = Max., I _{OUT} = 0 mA, f = f _{MAX}	Com. Ind.	— —	175 175	— —	160 160	— —	150 150	— —	150 150	mA
I _{SB1}	TTL Standby Current (TTL Inputs)	V _{CC} = Max., V _{IN} = V _{IH} or V _{IL} CE1 ≥ V _{IH} or CE2 ≤ V _{IL} , f = 0	Com. Ind.	— —	40 60	— —	40 60	— —	40 60	— —	40 60	mA
I _{SB2}	CMOS Standby Current (CMOS Inputs)	V _{CC} = Max., CE1 ≥ V _{CC} - 0.2V, CE2 ≤ 0.2V, V _{IN} ≥ V _{CC} - 0.2V, or V _{IN} ≤ 0.2V, f = 0	Com. Ind.	— —	250 500	— —	250 500	— —	250 500	— —	250 500	μA

Notes:

1. At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range, Standard and Low Power)

Symbol	Parameter	-12 ns		-15 ns		-20 ns		-25 ns		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t_{RC}	Read Cycle Time	12	—	15	—	20	—	25	—	ns
t_{AA}	Address Access Time	—	12	—	15	—	20	—	25	ns
t_{OHA}	Output Hold Time	3	—	3	—	3	—	3	—	ns
t_{ACE1}	$\overline{CE1}$ Access Time	—	12	—	15	—	20	—	25	ns
t_{ACE2}	$\overline{CE2}$ Access Time	—	12	—	15	—	20	—	25	ns
t_{DOE}	$\overline{OE}$ Access Time	—	6	—	7	—	9	—	9	ns
$t_{LZOE}^{(2)}$	$\overline{OE}$ to Low-Z Output	0	—	0	—	0	—	0	—	ns
$t_{HZOE}^{(2)}$	$\overline{OE}$ to High-Z Output	0	6	0	6	0	7	0	10	ns
$t_{LZCE1}^{(2)}$	$\overline{CE1}$ to Low-Z Output	2	—	2	—	3	—	3	—	ns
$t_{LZCE2}^{(2)}$	$\overline{CE2}$ to Low-Z Output	2	—	2	—	3	—	3	—	ns
$t_{HZCE}^{(2)}$	$\overline{CE1}$ or $\overline{CE2}$ to High-Z Output	0	7	0	8	0	9	0	10	ns
$t_{PU}^{(3)}$	$\overline{CE1}$ or $\overline{CE2}$ to Power-Up	0	—	0	—	0	—	0	—	ns
$t_{PD}^{(3)}$	$\overline{CE1}$ or $\overline{CE2}$ to Power-Down	—	12	—	12	—	18	—	20	ns

Notes:

1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1a.
2. Tested with the load in Figure 1b. Transition is measured ± 500 mV from steady-state voltage. Not 100% tested.
3. Not 100% tested.

AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	3 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1a and 1b

AC TEST LOADS

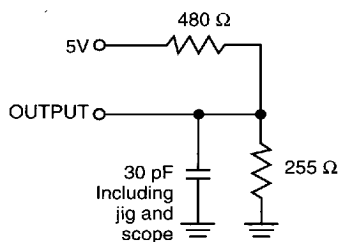


Figure 1a.

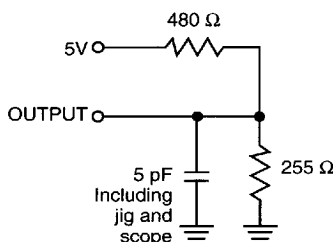
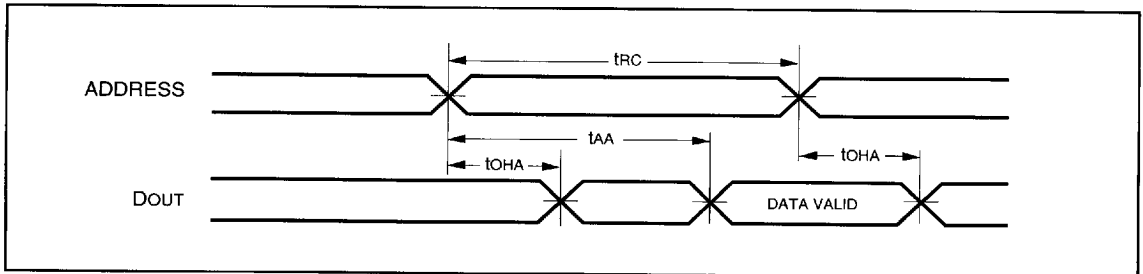


Figure 1b.

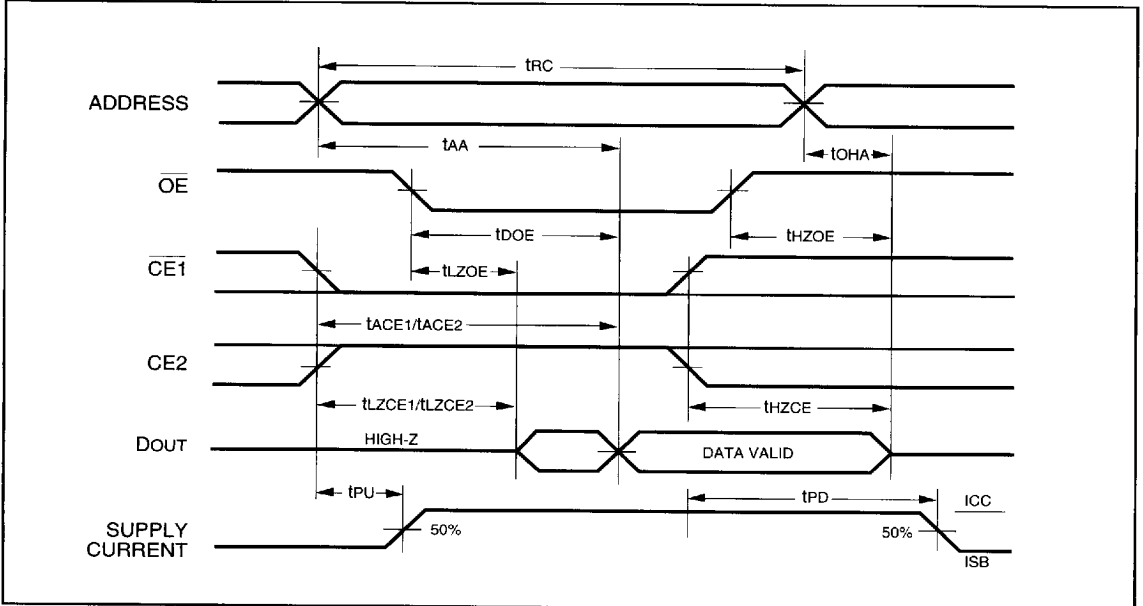
AC WAVEFORMS

READ CYCLE NO. 1^(1,2)



2

READ CYCLE NO. 2^(1,3)



Notes:

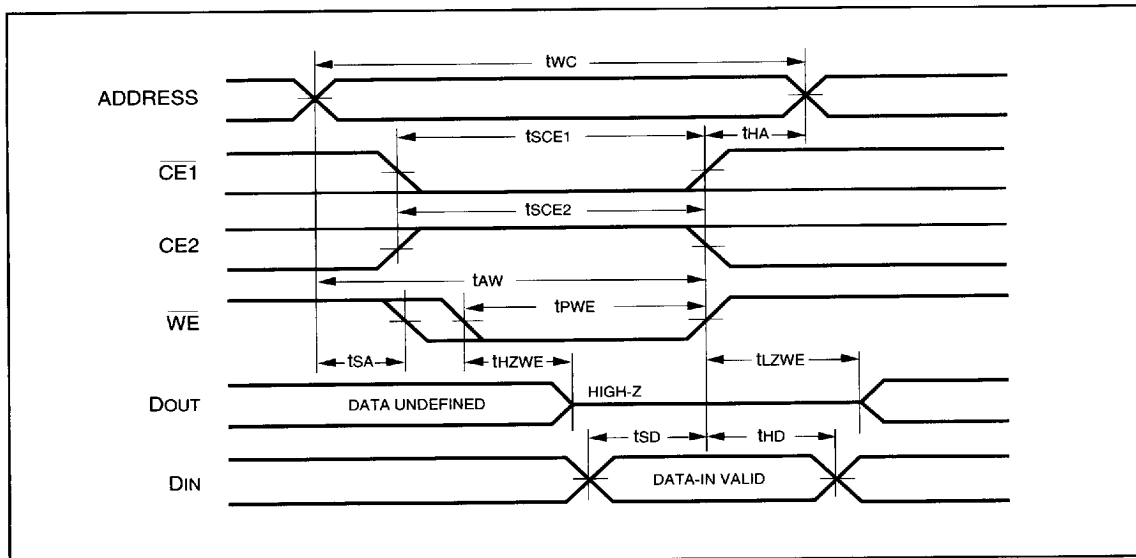
1. $\overline{WE}$ is HIGH for a Read Cycle.
2. The device is continuously selected. $\overline{OE}$, $\overline{CE1} = V_{IL}$, $CE2 = V_{IH}$.
3. Address is valid prior to or coincident with $\overline{CE1}$ LOW and $CE2$ HIGH transitions.

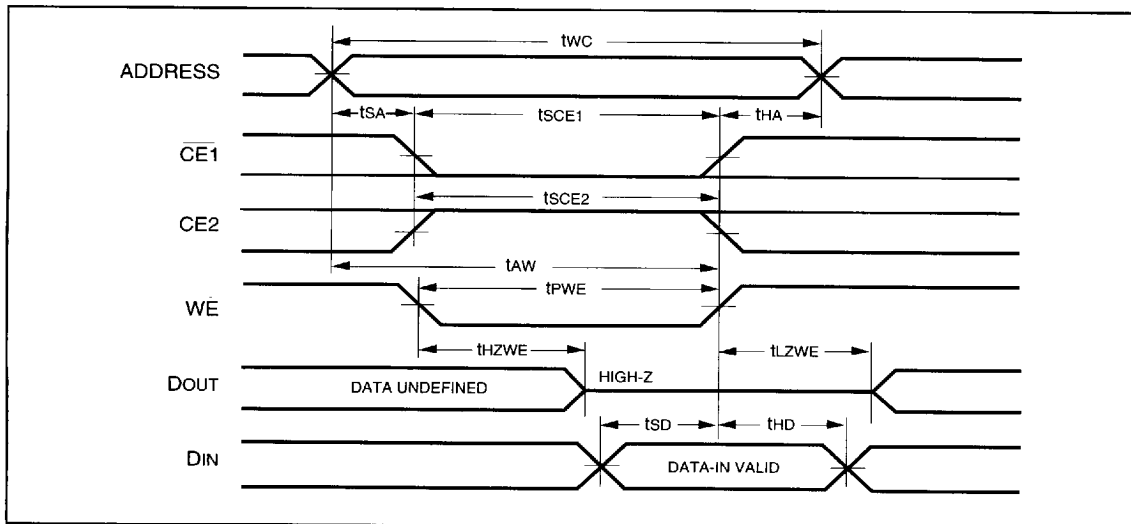
WRITE CYCLE SWITCHING CHARACTERISTICS^(1,3) (Over Operating Range, Standard and Low Power)

Symbol	Parameter	-12 ns		-15 ns		-20 ns		-25 ns		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _{WC}	Write Cycle Time	12	—	15	—	20	—	25	—	ns
t _{SCE1}	CE1 to Write End	10	—	12	—	15	—	20	—	ns
t _{SCE2}	CE2 to Write End	10	—	12	—	15	—	20	—	ns
t _{AW}	Address Setup Time to Write End	10	—	12	—	15	—	20	—	ns
t _{HA}	Address Hold from Write End	0	—	0	—	0	—	0	—	ns
t _{SA}	Address Setup Time	0	—	0	—	0	—	0	—	ns
t _{PWE⁽⁴⁾}	WE Pulse Width	10	—	10	—	12	—	15	—	ns
t _{SD}	Data Setup to Write End	7	—	8	—	10	—	12	—	ns
t _{HD}	Data Hold from Write End	0	—	0	—	0	—	0	—	ns
t _{HZWE⁽²⁾}	WE LOW to High-Z Output	—	7	—	7	—	10	—	12	ns
t _{LZWE⁽²⁾}	WE HIGH to Low-Z Output	2	—	2	—	2	—	2	—	ns

Notes:

1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1a.
2. Tested with the load in Figure 1b. Transition is measured ± 500 mV from steady-state voltage. Not 100% tested.
3. The internal write time is defined by the overlap of CE1 LOW, CE2 HIGH and WE LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
4. Tested with OE HIGH.

AC WAVEFORMS**WRITE CYCLE NO. 1 ($\overline{WE}$ Controlled)^(1,2)**

WRITE CYCLE NO. 2 ($\overline{\text{CE1}}$, CE2 Controlled)^(1,2)

Notes:

1. The internal write time is defined by the overlap of $\overline{\text{CE1}}$ LOW, CE2 HIGH and $\overline{\text{WE}}$ LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
2. I/O will assume the High-Z state if $\overline{\text{OE}} = V_{\text{IH}}$.

IS61C1024 STANDARD VERSION
ORDERING INFORMATION
Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
12	IS61C1024-12JR	300-mil Plastic SOJ
12	IS61C1024-12NR	300-mil Plastic DIP
12	IS61C1024-12KR	400-mil Plastic SOJ
12	IS61C1024-12MR	400-mil Plastic DIP
15	IS61C1024-15J	300-mil Plastic SOJ
15	IS61C1024-15N	300-mil Plastic DIP
15	IS61C1024-15K	400-mil Plastic SOJ
15	IS61C1024-15M	400-mil Plastic DIP
20	IS61C1024-20J	300-mil Plastic SOJ
20	IS61C1024-20N	300-mil Plastic DIP
20	IS61C1024-20K	400-mil Plastic SOJ
20	IS61C1024-20M	400-mil Plastic DIP
25	IS61C1024-25J	300-mil Plastic SOJ
25	IS61C1024-25N	300-mil Plastic DIP
25	IS61C1024-25K	400-mil Plastic SOJ
25	IS61C1024-25M	400-mil Plastic DIP

IS61C1024 STANDARD VERSION
ORDERING INFORMATION
Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
12	IS61C1024-12JRI	300-mil Plastic SOJ
12	IS61C1024-12NRI	300-mil Plastic DIP
12	IS61C1024-12KRI	400-mil Plastic SOJ
12	IS61C1024-12MRI	400-mil Plastic DIP
15	IS61C1024-15JI	300-mil Plastic SOJ
15	IS61C1024-15NI	300-mil Plastic DIP
15	IS61C1024-15KI	400-mil Plastic SOJ
15	IS61C1024-15MI	400-mil Plastic DIP
20	IS61C1024-20JI	300-mil Plastic SOJ
20	IS61C1024-20NI	300-mil Plastic DIP
20	IS61C1024-20KI	400-mil Plastic SOJ
20	IS61C1024-20MI	400-mil Plastic DIP
25	IS61C1024-25JI	300-mil Plastic SOJ
25	IS61C1024-25NI	300-mil Plastic DIP
25	IS61C1024-25KI	400-mil Plastic SOJ
25	IS61C1024-25MI	400-mil Plastic DIP

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Rev. D 1095
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2-71

IS61C1024L LOW POWER VERSION

ORDERING INFORMATION

Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
12	IS61C1024L-12JR	300-mil Plastic SOJ
12	IS61C1024L-12NR	300-mil Plastic DIP
12	IS61C1024L-12KR	400-mil Plastic SOJ
12	IS61C1024L-12MR	400-mil Plastic DIP
15	IS61C1024L-15J	300-mil Plastic SOJ
15	IS61C1024L-15N	300-mil Plastic DIP
15	IS61C1024L-15K	400-mil Plastic SOJ
15	IS61C1024L-15M	400-mil Plastic DIP
20	IS61C1024L-20J	300-mil Plastic SOJ
20	IS61C1024L-20N	300-mil Plastic DIP
20	IS61C1024L-20K	400-mil Plastic SOJ
20	IS61C1024L-20M	400-mil Plastic DIP
25	IS61C1024L-25J	300-mil Plastic SOJ
25	IS61C1024L-25N	300-mil Plastic DIP
25	IS61C1024L-25K	400-mil Plastic SOJ
25	IS61C1024L-25M	400-mil Plastic DIP

IS61C1024L LOW POWER VERSION

ORDERING INFORMATION

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
12	IS61C1024L-12JRI	300-mil Plastic SOJ
12	IS61C1024L-12NRI	300-mil Plastic DIP
12	IS61C1024L-12KRI	400-mil Plastic SOJ
12	IS61C1024L-12MRI	400-mil Plastic DIP
15	IS61C1024L-15JI	300-mil Plastic SOJ
15	IS61C1024L-15NI	300-mil Plastic DIP
15	IS61C1024L-15KI	400-mil Plastic SOJ
15	IS61C1024L-15MI	400-mil Plastic DIP
20	IS61C1024L-20JI	300-mil Plastic SOJ
20	IS61C1024L-20NI	300-mil Plastic DIP
20	IS61C1024L-20KI	400-mil Plastic SOJ
20	IS61C1024L-20MI	400-mil Plastic DIP
25	IS61C1024L-25JI	300-mil Plastic SOJ
25	IS61C1024L-25NI	300-mil Plastic DIP
25	IS61C1024L-25KI	400-mil Plastic SOJ
25	IS61C1024L-25MI	400-mil Plastic DIP